

P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

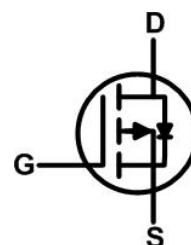
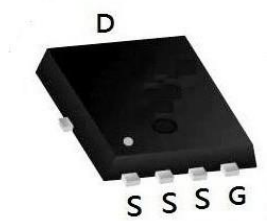
BVDSS	RDSON	ID
-30V	15mΩ	-30A

Description

The XR 30P03D is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XR 30P03D meet the RoHS and Gree Product requirement 100% EAS guaranteed with full function reliability approved.

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	-30	A
	$T_C = 100^\circ\text{C}$		-15.8	
Pulsed Drain Current ¹		I_{DM}	-100	A
Single Pulse Avalanche Energy ²		EAS	26.5	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	22	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	79	$^\circ\text{C/W}$
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	5.7	$^\circ\text{C/W}$

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Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Gate-body Leakage current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
	T _J =100°C			-	-	-100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = -10V, I _D = -10A	-	15	20	mΩ
			V _{GS} = -4.5V, I _D = -6A	-	22.5	30	
Forward Transconductance ⁴		g _{fs}	V _{DS} = -10V, I _D = -10A	-	23.5	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = -15V, V _{GS} =0V, f =1MHz	-	980	-	pF
Output Capacitance		C _{oss}		-	137	-	
Reverse Transfer Capacitance		C _{rss}		-	113	-	
Gate Resistance		R _g	f =1MHz	-	10.5	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = -10V,V _{DS} = -15V, I _D = -10A	-	20	-	nC
Gate-Source Charge		Q _{gs}		-	3	-	
Gate-Drain Charge		Q _{gd}		-	5.5	-	
Turn-On Delay Time		t _{d(on)}	V _{GS} = -10V, V _{DD} = -15V, R _G = 3Ω, I _D = -10A	-	7.5	-	ns
Rise Time		t _r		-	16	-	
Turn-Off Delay Time		t _{d(off)}		-	49	-	
Fall Time		t _f		-	32	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F = -10A, dI _F /dt = 100A/μs	-	21	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	12.5	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = -10A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	-30	A

Note :

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = -25V, V_{GS} = -10V, L = 0.1\text{mH}, I_{AS} = -23A$.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Performance Characteristics

Figure1: Output Characteristics

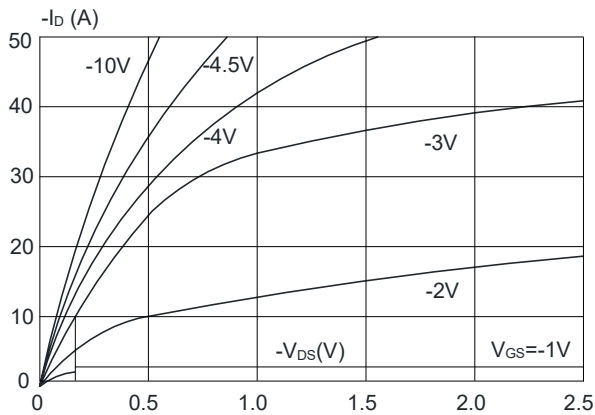


Figure 2: Typical Transfer Characteristics

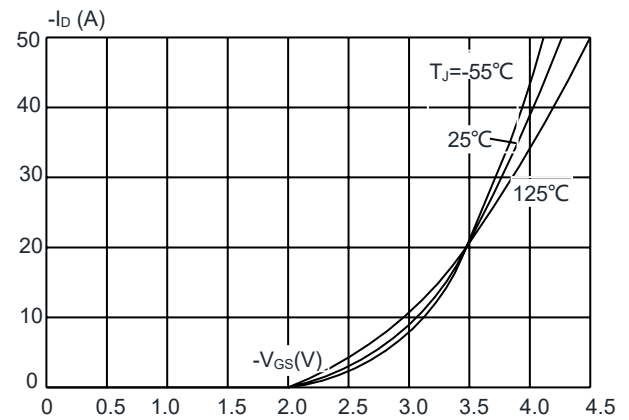


Figure 3: On-resistance vs. Drain Current

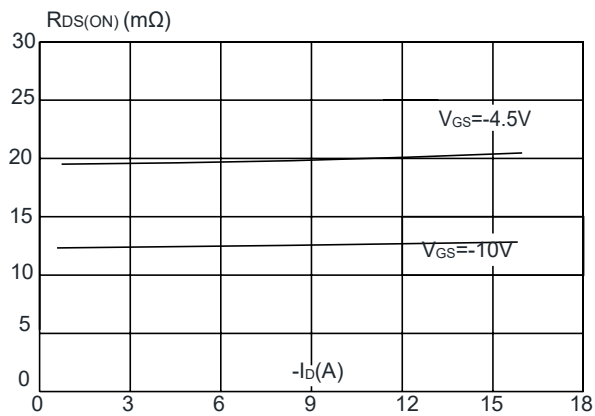


Figure 4: Body Diode Characteristics

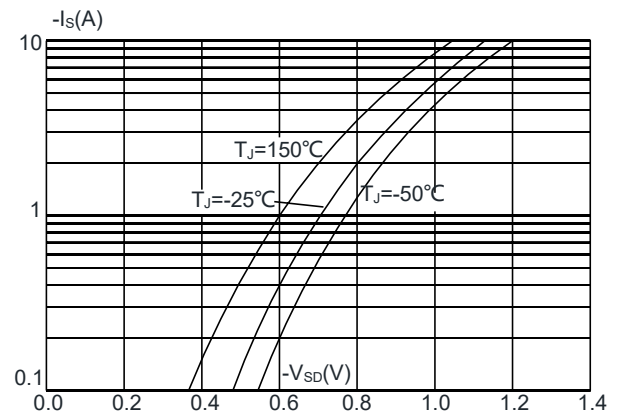


Figure 5: Gate Charge Characteristics

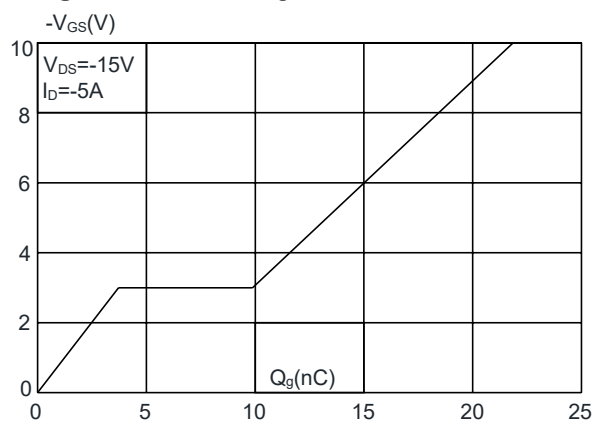
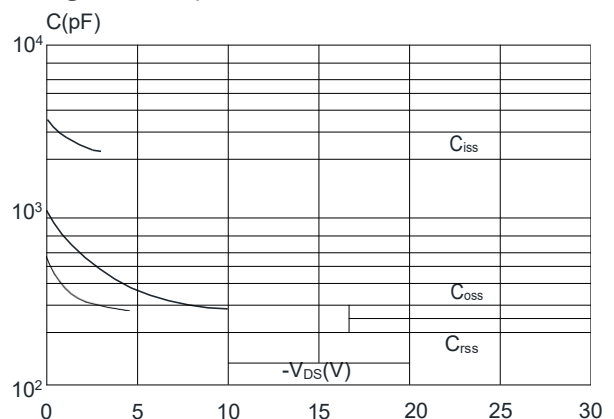


Figure 6: Capacitance Characteristics



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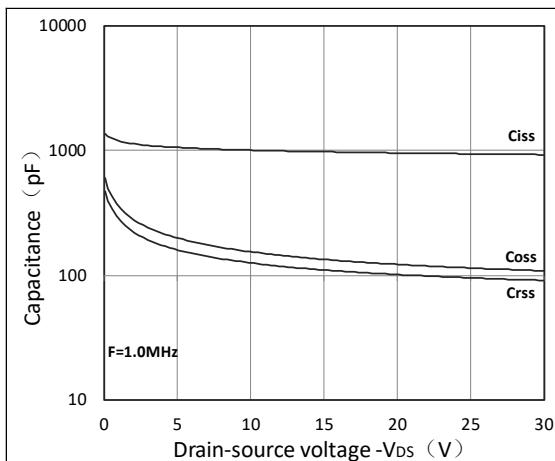


Figure 7. Capacitance Characteristics

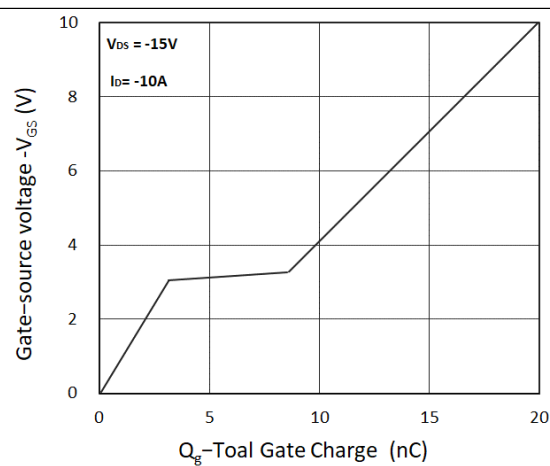


Figure 8. Gate Charge Characteristics

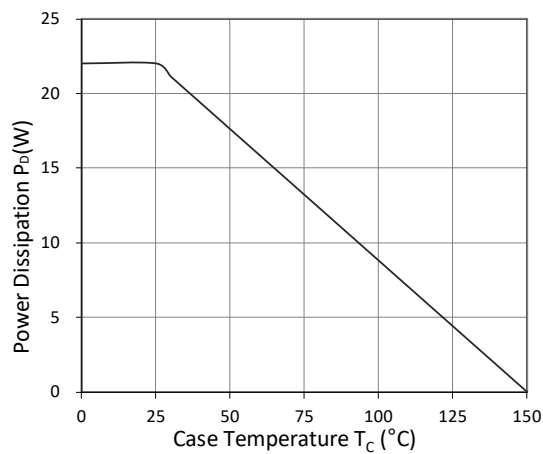


Figure 9. Power Dissipation

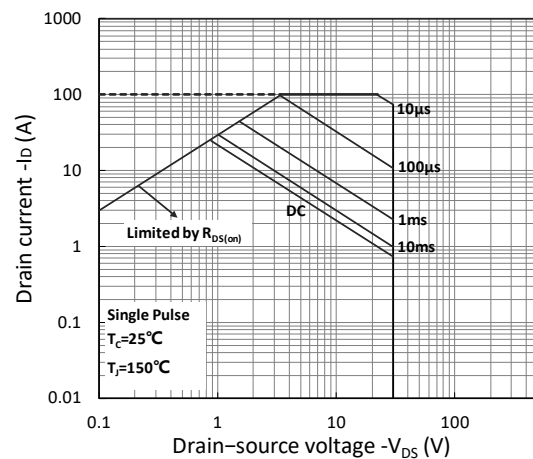


Figure 10. Safe Operating Area

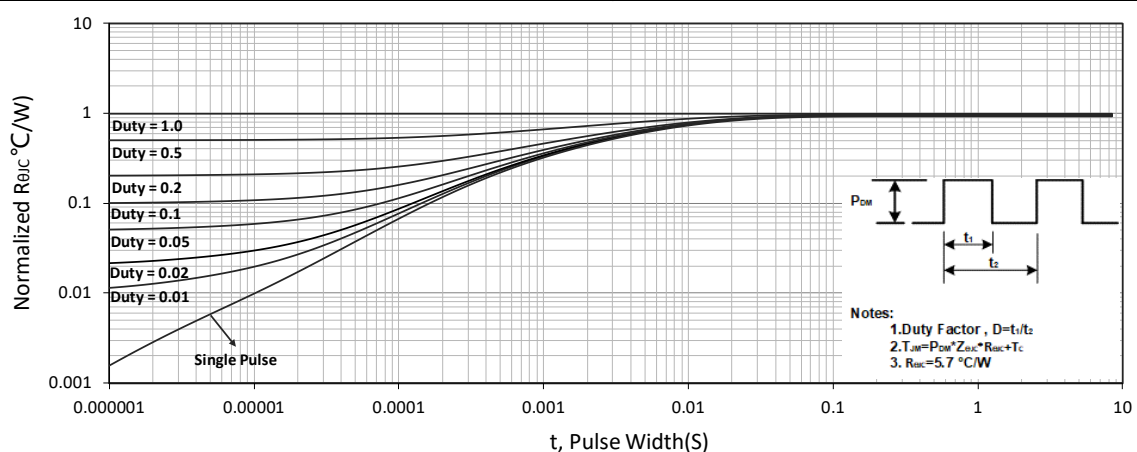
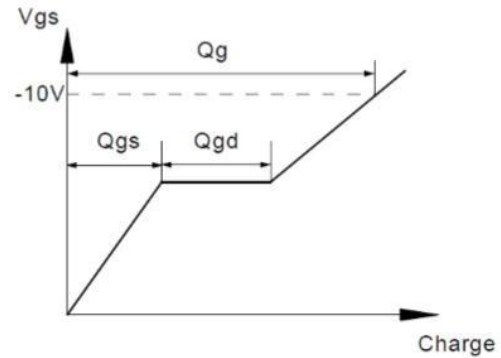
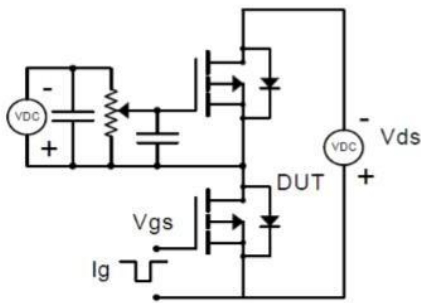


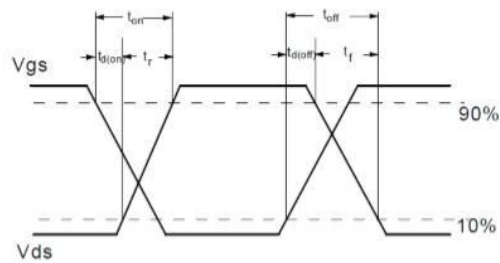
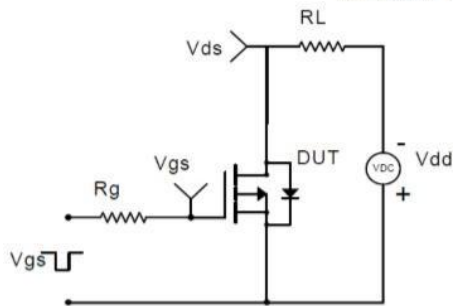
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

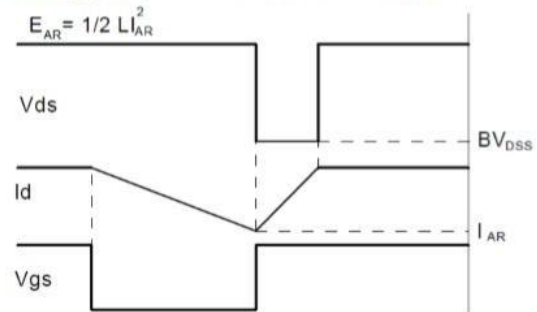
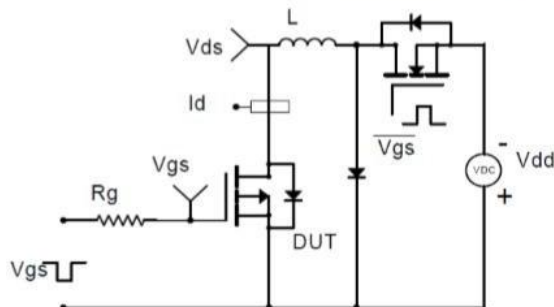
Gate Charge Test Circuit & Waveform



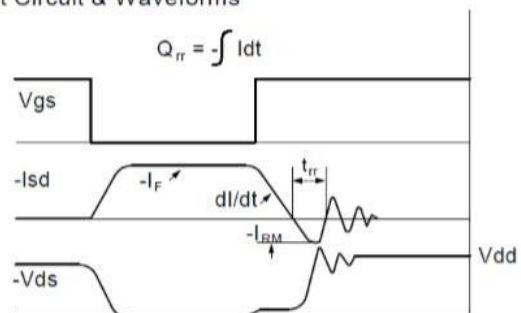
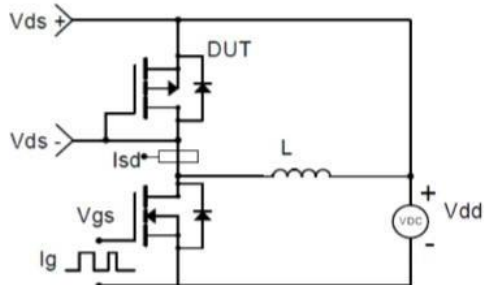
Resistive Switching Test Circuit & Waveforms



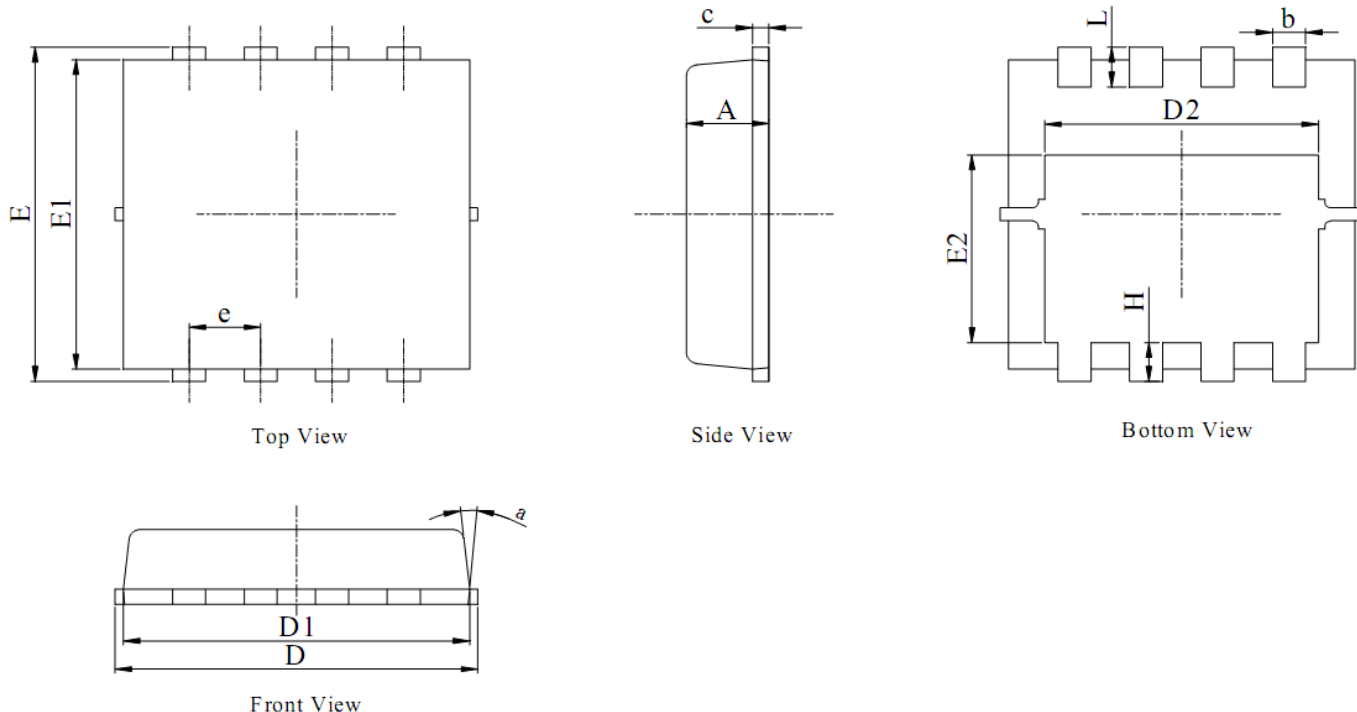
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



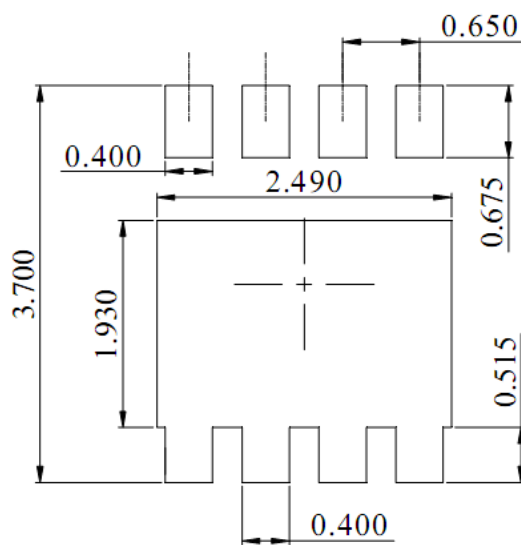
Package Mechanical Data-PDFN3333-8L-Single



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS